

Cong Ye

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Memristor Based on TiO ₂ /Al ₂ O ₃ Bilayer as Flexible Artificial Synapse for Neuromorphic Electronics. IEEE Transactions on Electron Devices, 2022, 69, 375-379.	3.0	21
2	Topochemical Synthesis of Copper Phosphide Nanoribbons for Flexible Optoelectronic Memristors (Adv. Funct. Mater. 14/2022). Advanced Functional Materials, 2022, 32, .	14.9	0
3	Brain-like synaptic memristor based on lithium-doped silicate for neuromorphic computing. Frontiers of Physics, 2022, 17, .	5.0	8
4	Optoelectronic Artificial Synapses Based on Two-Dimensional Transitional-Metal Trichalcogenide. ACS Applied Materials & Interfaces, 2021, 13, 30797-30805.	8.0	41
5	HfO ₂ -Based Memristor as an Artificial Synapse for Neuromorphic Computing with Tri-layer HfO ₂ /BiFeO ₃ /HfO ₂ Design. Advanced Functional Materials, 2021, 31, 2107131.	14.9	63
6	C ₂ N/BlueP van der Waals hetero-structure: an efficient photocatalytic water splitting 2D material. Physical Chemistry Chemical Physics, 2020, 22, 1485-1492.	2.8	34
7	An indirect way to achieve comprehensive performance improvement of resistive memory: when hafnium meets ITO in an electrode. Nanoscale, 2020, 12, 3267-3272.	5.6	23
8	A Robust and Low-Power Bismuth Doped Tin Oxide Memristor Derived from Coaxial Conductive Filaments. Small, 2020, 16, e2004619.	10.0	21
9	Black phosphorus field effect transistors stable in harsh conditions via surface engineering. Applied Physics Letters, 2020, 117, .	3.3	7
10	Two-Dimensional As/BlueP van der Waals Hetero-Structure as a Promising Photocatalyst for Water Splitting: A DFT Study. Coatings, 2020, 10, 1160.	2.6	9
11	Black Phosphorus Based Multicolor Light-Modulated Transparent Memristor with Enhanced Resistive Switching Performance. ACS Applied Materials & Interfaces, 2020, 12, 25108-25114.	8.0	32
12	Resistive switching performance improvement of InGaZnO-based memory device by nitrogen plasma treatment. Journal of Materials Science and Technology, 2020, 49, 1-6.	10.7	33
13	High Voltage Gain WSe ₂ Complementary Compact Inverter With Buried Gate for Local Doping. IEEE Electron Device Letters, 2020, 41, 944-947.	3.9	14
14	Flexible Poly(Vinyl Alcohol)-Graphene Oxide Hybrid Nanocomposite Based Cognitive Memristor with Pavlovian-Conditioned Reflex Activities. Advanced Electronic Materials, 2020, 6, 1901402.	5.1	31
15	Designing High-Performance Storage in HfO ₂ /BiFeO ₃ Memristor for Artificial Synapse Applications. Advanced Electronic Materials, 2020, 6, 1901012.	5.1	66
16	Flexible HfO ₂ /Graphene Oxide Selector With Fast Switching and High Endurance. IEEE Journal of the Electron Devices Society, 2019, 7, 1125-1128.	2.1	3
17	Bilayered Oxide-Based Cognitive Memristor with Brain-Inspired Learning Activities. Advanced Electronic Materials, 2019, 5, 1900439.	5.1	43
18	Role of Oxygen Vacancies at the TiO ₂ /HfO ₂ Interface in Flexible Oxide-Based Resistive Switching Memory. Advanced Electronic Materials, 2019, 5, 1800833.	5.1	105

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19	An improved analytical model for the statistics of SET emergence point in HfO ₂ memristive device. AIP Advances, 2019, 9, 025118.	1.3	1
20	Hafnium nanocrystals observed in a HfTiO compound film bring about excellent performance of flexible selectors in memory integration. Nanoscale, 2019, 11, 20792-20796.	5.6	10
21	Exploring the role of nitrogen incorporation in ZrO ₂ resistive switching film for enhancing the device performance. Journal of Alloys and Compounds, 2019, 775, 1301-1306.	5.5	26
22	Impact of Forming Compliance Current on Storage Window Induced by a Gadolinium Electrode in Oxide-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2018, 65, 96-100.	3.0	10
23	Exploration of highly enhanced performance and resistive switching mechanism in hafnium doping ZnO memristive device. Semiconductor Science and Technology, 2018, 33, 085013.	2.0	13
24	High performance, self-powered ultraviolet photodetector based on a ZnO nanoarrays/GaN structure with a CdS insert layer. New Journal of Chemistry, 2017, 41, 4901-4907.	2.8	58
25	High-performance ultraviolet-visible tunable perovskite photodetector based on solar cell structure. Science China Materials, 2017, 60, 407-414.	6.3	42
26	Effect of sputtering atmosphere on the characteristics of ZrO _x resistive switching memory. Semiconductor Science and Technology, 2017, 32, 055016.	2.0	10
27	Boosting the performance of resistive switching memory with a transparent ITO electrode using supercritical fluid nitridation. RSC Advances, 2017, 7, 11585-11590.	3.6	21
28	A high-performance self-powered broadband photodetector based on a CH ₃ NH ₃ Pb ₃ perovskite/ZnO nanorod array heterostructure. Journal of Materials Chemistry C, 2016, 4, 7302-7308.	5.5	159
29	Enhanced resistive switching performance for bilayer HfO ₂ /TiO ₂ resistive random access memory. Semiconductor Science and Technology, 2016, 31, 105005.	2.0	49
30	Improved performance of ITO/TiO ₂ /HfO ₂ /Pt random resistive accessory memory by nitrogen annealing treatment. Microelectronics Reliability, 2016, 57, 34-38.	1.7	15
31	Physical Mechanism and Performance Factors of Metal Oxide Based Resistive Switching Memory: A Review. Journal of Materials Science and Technology, 2016, 32, 1-11.	10.7	94
32	Phosphorus-doping-induced rectifying behavior in armchair graphene nanoribbons devices. Journal of Applied Physics, 2014, 115, .	2.5	18
33	The electronic transport behavior of hybridized zigzag graphene and boron nitride nanoribbons. Journal of Applied Physics, 2014, 115, .	2.5	18
34	Negative differential resistance behavior in phosphorus-doped armchair graphene nanoribbon junctions. Journal of Applied Physics, 2014, 115, .	2.5	26
35	Low-power bipolar resistive switching TiN/HfO ₂ /ITO memory with self-compliance current phenomenon. Applied Physics Express, 2014, 7, 034101.	2.4	70
36	Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. IEEE Electron Device Letters, 2013, 34, 502-504.	3.9	55

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37	Influence of Source and Drain Electrodes on Device Performance of ZnO Thin Film Transistors. Integrated Ferroelectrics, 2013, 142, 73-78.	0.7	0
38	EFFECT OF GATE ELECTRODES ON STRUCTURE AND ELECTRICAL PROPERTIES OF SPUTTERED HfO ₂ THIN FILMS. Modern Physics Letters B, 2012, 26, 1250161.	1.9	0
39	Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical CO_2 Fluid Treatment. IEEE Electron Device Letters, 2012, 33, 1693-1695.	3.9	45
40	Dielectric property and electrical conduction mechanism of ZrO ₂ -TiO ₂ composite thin films. Journal of Materials Science: Materials in Electronics, 2012, 23, 174-179.	2.2	8
41	Evidence of interface conversion and electrical characteristics improvement of ultra-thin HfTiO films upon rapid thermal annealing. Applied Physics Letters, 2011, 99, 182904.	3.3	11
42	Growth and magnetic properties of single crystalline Ni nanowire arrays prepared by pulse DC electrodeposition. Science China: Physics, Mechanics and Astronomy, 2011, 54, 1244-1248.	5.1	6
43	Drive current and hot carrier reliability improvements of high-aspect-ratio n-channel fin-shaped field effect transistor with high-tensile contact etching stop layer. Applied Physics Letters, 2011, 99, .	3.3	7
44	Composition dependence of band alignment and dielectric constant for Hf _{1-x} Ti _x O ₂ thin films on Si (100). Journal of Applied Physics, 2010, 107, 104103.	2.5	38
45	Improved thermal stability, interface, and electrical properties of HfO ₂ films prepared by pulsed laser deposition using <i>in situ</i> ionized nitrogen. Applied Physics Letters, 2009, 95, .	3.3	22
46	Topochemical Synthesis of Copper Phosphide Nanoribbons for Flexible Optoelectronic Memristors. Advanced Functional Materials, 0, , 2110900.	14.9	11